

Isc N-Channel MOSFET Transistor

SPU04N60C3

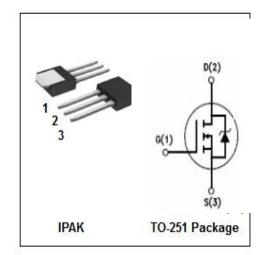
• FEATURES

- With To-251(IPAK) package
- · New revolutionary high voltage technology
- · Ultra low gate charge
- High peak current capability
- · Improved transconductance
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

· Switching applications

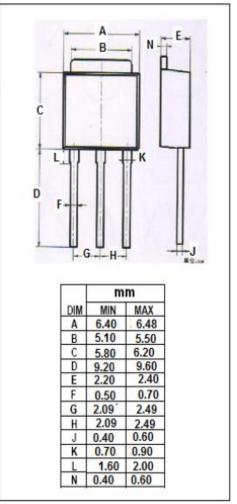


• ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage 600		V	
V _{GSS}	Gate-Source Voltage	±30	V	
I _D	Drain Current-Continuous@Tc=25℃ Tc=125℃	4.5 2.8	А	
I_{DM}	Drain Current-Single Pulsed 13.5		А	
P_D	Total Dissipation @T _C =25°C 50		W	
T _{ch}	Max. Operating Junction Temperature	Temperature 150		
T _{stg}	Storage Temperature	-55~150	$^{\circ}$	



SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	2.5	°C/W
Rth(ch-a)	Channel-to-ambient thermal resistance	75	°C/W





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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 0.25mA	600			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = ±30V; I _D =0.2mA	2.1		3.9	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =2.8A		890	950	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} = 0V			±0.1	μА
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 600V; V _{GS} = 0V; T _J =25°C T _J =125°C			1 50	μА
V _{SDF}	Diode forward voltage	I _{SD} =4.5A, V _{GS} = 0 V			1.2	V

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